

isc N-Channel MOSFET Transistor

AOB15S65

FEATURES

- Drain Current –I_D= 15A@ T_C=25℃
- · Drain Source Voltage-: V_{DSS}= 650V(Min)
- Static Drain-Source On-Resistance
- : R_{DS(on)} = 0.78 Ω (Max)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

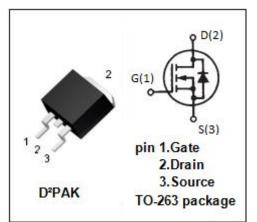
DESCRIPTION

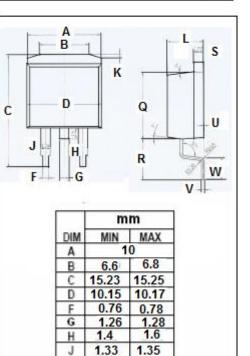
· Designed for use in switch mode power supplies and general purpose applications.

| ABSOLUTE MAXIMUM RATINGS(Ta=25°C) | | | | | | | |
|-----------------------------------|--|---------|------|--|--|--|--|
| SYMBOL | PARAMETER VAL | | UNIT | | | | |
| V _{DSS} | Drain-Source Voltage | 650 | V | | | | |
| V _{GS} | Gate-Source Voltage-Continuous ±30 | | V | | | | |
| ID | Drain Current-Continuous 15 | | А | | | | |
| I _{DM} | Drain Current-Single Pluse | 60 | А | | | | |
| P _D | Total Dissipation @T _c =25℃ | 208 | W | | | | |
| TJ | Max. Operating Junction Temperature | -55~150 | °C | | | | |
| T _{stg} | Storage Temperature | -55~150 | °C | | | | |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------------|--------------------------------------|-----|------|
| R _{th j-c} | Thermal Resistance, Junction to Case | 0.6 | °C/W |





0.6

4.8

8.71

5.30 1.28

0.2

0.39

2.82

K

0

R

s

U

v W 0.4

4.6

8.69

5.28

1.26

0.0

0.37

2.80

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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYPE | МАХ | UNIT |
|----------------------|---------------------------------|--|-----|------|------|------|
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0; I _D = 0.25mA | 650 | | | V |
| V _{GS} (th) | Gate Threshold Voltage | V _{DS} = 5V; I _D = 0.25mA | 2.6 | | 4.0 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D = 7.5A | | | 0.29 | Ω |
| l _{GSS} | Gate-Body Leakage Current | V _{GS} = ±30V;V _{DS} = 0 | | | ±100 | nA |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = 650V; V _{GS} = 0 V _{DS} = 520V; V _{GS} = 0;T _J =150°C | | 10 | 1 | μA |
| V _{SD} | Forward On-Voltage | I _S = 7.5A; V _{GS} = 0 | | 0.82 | | V |

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